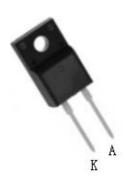
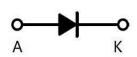


FRED Ultrafast Soft Recovery Diode, 30A

Features:

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low power loss, less RFI and EMI
- Low I_R value
- High surge capacity
- Epitaxial chip construction





Product Summary		
V_R	1200 V	
lf(AV)	30A	
t _{rr}	32 ns	

Description/Applications

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery behavior of the diodes offers the need as snubber in most applications. These devices are ideally suited for HF welding power converters and other applications where the switching losses are not significant portion of the total losses.

Absolute Maximum Ratings				
Parameter	Symbol	Test Conditions	Values	Units
Repetitive peak reverse voltage	V_{RRM}		1200	V
Continuous forward current	lf(AV)	Tc =110°C	30	
Single pulse forward current	I _{FSM}	Tc =25°C	150	А
Maximum repetitive forward current	I _{FRM}	Square wave, 20kHZ	60	
Operating junction	Тј		175	°C
Storage temperatures	Tstg		-55 to +175	°C

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Parameter	Symbol	Test Conditions	Min	Тур.	Max.	Units
Breakdown voltage Blocking voltage	V _{BR} ,	I _R =100μA	1200			
Forward voltage (Per Diode)		I _F =30A		2.10	2.70	V
	V _F	I _F =30A, Tj =125°C		1.85	2.50	
Reverse leakage		VR= VRRM			20	
current(Per Diode)	Tj=150°C, V _R =600V			200	μ Α	
Reverse recovery time(Per Diode)	,	I _F =0.5A, I _R =1A, I _{RR} =0.25A		50	70	nc
	t _{rr}	I _F =1A,V _R =30V, di/ <i>dt</i> =200A/us		32	50	ns

Thermal characteristics

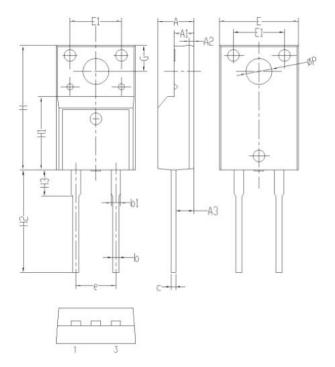
Paramter	Symbol	Тур	Units
Junction-to-Case	$R_{ heta$ JC	0.8	°C/W

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Package Information

TO-220F-2L PACKAGE



Symbol	Dimensions(millimeters)	
Symbol	Min.	Max.
Α	4.35	4.75
A1	2.30	2.70
A2	0.40	0.80
A3	2.10	2.50
b	0.60	1.00
b1	1.00	1.40
С	0.30	0.70
е	4.60	5.40
E	9.80	10.2
E1	6.30	6.70
Н	15.6	16.0
H1	8.80	9.20
H2	12.9	13.5
H3	3.10	3.50
G	3.10	3.50
ФР	3.10	3.50

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